

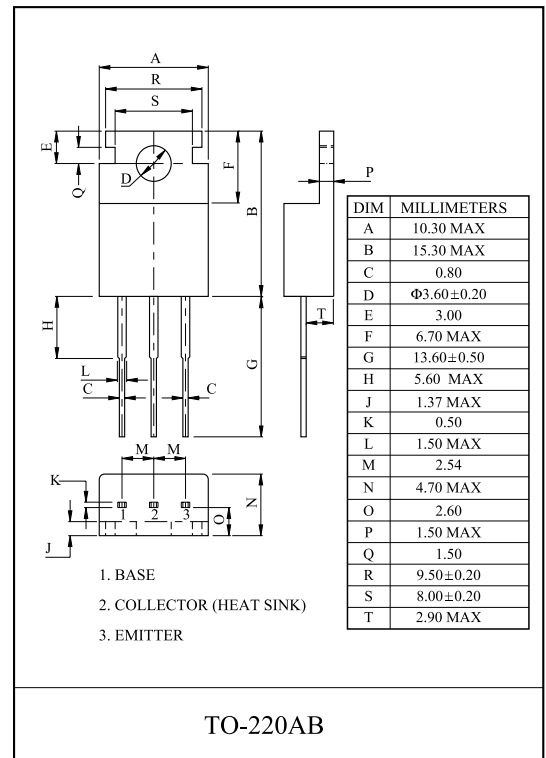
MONOLITHIC CONSTRUCTION WITH BUILT IN
BASE-EMITTER SHUNT RESISTORS INDUSTRIAL USE.

FEATURES

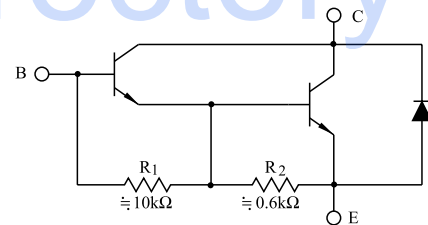
- High DC Current Gain.
: $h_{FE}=1000(\text{Min.})$, @ $V_{CE}=4V$, $I_C=1A$.
- Low Collector-Emitter Saturation Voltage.
- Complementary to TIP117.

MAXIMUM RATING (Ta=25)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V_{CBO}	100	V
Collector-Emitter Voltage	V_{CEO}	100	V
Emitter-Base Voltage	V_{EBO}	5	V
Collector Current	DC	I_C	A
	Pulse	I_{CP}	
Base Current	DC	I_B	50 mA
Collector Power Dissipation	Ta=25	P_C	W
	Tc=25		
Junction Temperature	T_j	150	
Storage Temperature Range	T_{stg}	-65 150	



EQUIVALENT CIRCUIT

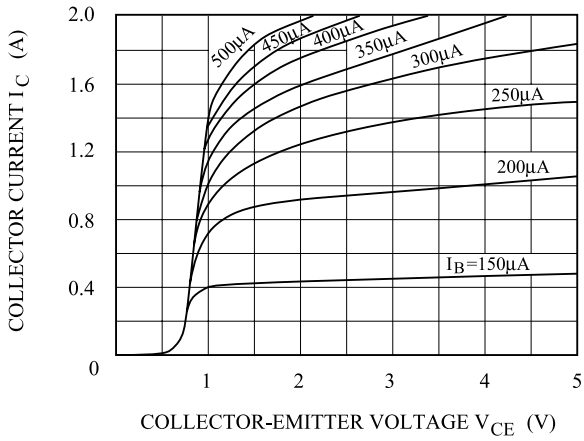


ELECTRICAL CHARACTERISTICS (Ta=25)

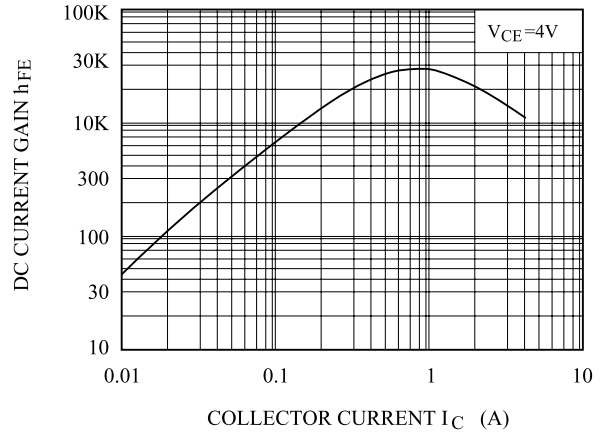
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I_{CEO}	$V_{CE}=50V, I_B=0$	-	-	2	mA
	I_{CBO}	$V_{CB}=100V, I_E=0$	-	-	1	
Emitter Cut-off Current	I_{EBO}	$V_{EB}=5V, I_C=0$	-	-	2	mA
DC Current Gain	h_{FE}	$V_{CE}=4V, I_C=1A$	1000	-	-	
		$V_{CE}=4V, I_C=2A$	500	-	-	
Collector-Emitter Sustaining Voltage	$V_{CEO(SUS)}$	$I_C=30mA, I_B=0$	100	-	-	V
Collector-Emitter Saturation Voltage	$V_{CE(sat)}$	$I_C=2A, I_B=8mA$	-	-	2.5	V
Base-Emitter On Voltage	$V_{BE(ON)}$	$V_{CE}=4V, I_C=2A$	-	-	2.8	V
Collector Output Capacitance	C_{ob}	$V_{CB}=10V, I_E=0, f=0.1MHz$	-	-	100	pF

TIP112

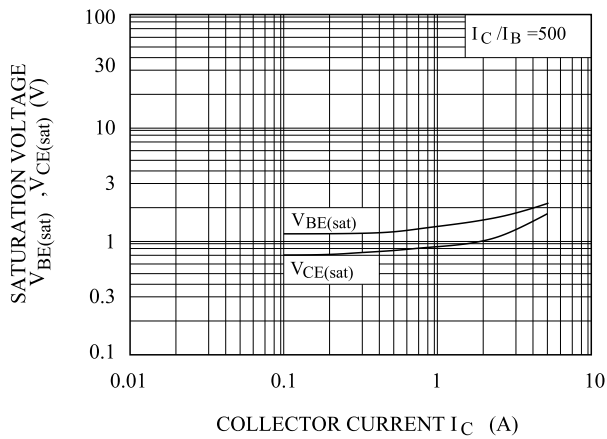
$I_C - V_{CE}$



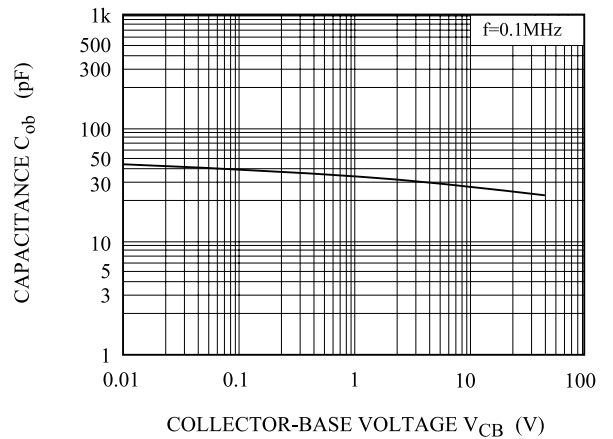
$h_{FE} - I_C$



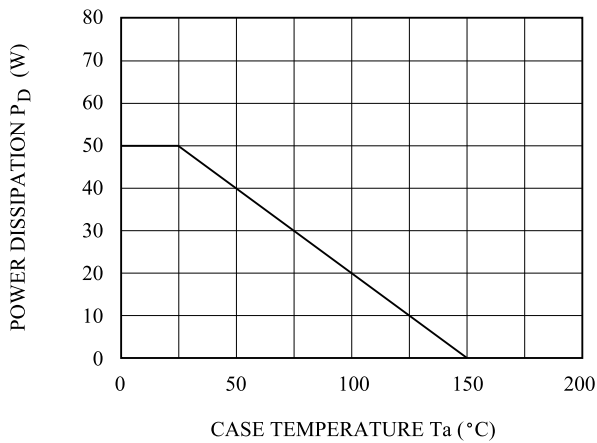
$V_{BE(sat)}, V_{CE(sat)} - I_C$



$C_{ob} - V_{CB}$



$P_D - T_a$



SAFE OPERATING AREA

